

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. P27127	Application No. 10/707,840		
INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)				Applicant Huiliong ZHU et al.			
				Filing Date January 16, 2004		Group 2811 2818	
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EXAMINER				/Dao Nguyen/		DATE CONSIDERED 01/08/2007	
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